

AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1-12. (Canceled)

13. (Currently amended) A pattern formation method comprising the steps of:

forming a resist film of a positive chemically amplified resist material; and

forming a resist pattern by developing said resist film with a developer after irradiating, through a mask, said resist film with exposing light having a light component entering said resist film at the Brewster's angle,

wherein said chemically amplified resist material includes a dissolution inhibitor for generating sulfonic acid through irradiation with light and a base polymer for generating sulfonic acid through irradiation with light, and

the dissolution inhibitor for generating sulfonic acid through irradiation with light is an ester of styrenesulfonic acid.

14-15. (Canceled)

16. (Currently amended) A pattern formation method comprising the steps of:

forming a resist film of a positive chemically amplified resist material; and

forming a resist pattern by developing said resist film with a developer after irradiating, through a mask, said resist film with exposing light having a light component entering said resist film at the Brewster's angle,

wherein said chemically amplified resist material includes a dissolution inhibitor for generating sulfonic acid through irradiation with light, and

the dissolution inhibitor for generating sulfonic acid through irradiation with light is an ester of styrenesulfonic acid.

17-18. (Canceled)

19. (Previously presented) The pattern formation method of Claim 16,
wherein said exposing light is UV, KrF excimer laser, ArF excimer laser, F₂ laser, ArKr laser, Ar₂ laser, Kr₂ laser or extreme UV.

20-23. (Canceled)

24. (Previously presented) The pattern formation method of Claim 13,
wherein the base polymer for generating sulfonic acid through irradiation with light is an ester of polyvinylsulfonic acid or polystyrenesulfonic acid.

25. (Canceled)

26. (Previously presented) The pattern formation method of Claim 13,
wherein the base polymer for generating sulfonic acid through irradiation with light is poly(styrenesulfonic acid-t-butyl ester) or poly(styrenesulfonic acid-2-methyl-2-adamantyl ester).

27-28. (Canceled)

29. (Previously presented) The pattern formation method of Claim 13,
wherein the dissolution inhibitor for generating sulfonic acid through irradiation with light is styrenesulfonic acid-t-butyl ester or styrenesulfonic acid-2-methyl-2-adamantyl ester.

30. (Previously presented) The pattern formation method of Claim 16,
wherein the dissolution inhibitor for generating sulfonic acid through irradiation with light is styrenesulfonic acid-t-butyl ester or styrenesulfonic acid-2-methyl-2-adamantyl ester.

31. (Canceled)

32. (Previously presented) A pattern formation method comprising the steps of:
forming a resist film of a positive chemically amplified resist material; and
forming a resist pattern by developing said resist film with a developer after irradiating, through a mask, said resist film with exposing light having a light component entering said resist film at the Brewster's angle,

wherein said chemically amplified resist material includes a dissolution inhibitor for generating carboxylic acid through irradiation with light, and

wherein the dissolution inhibitor for generating carboxylic acid through irradiation with light is an ester of acrylic acid, methacrylic acid or α -trifluoromethylacrylic acid.

33. (Previously presented) A pattern formation method comprising the steps of:
forming a resist film of a positive chemically amplified resist material; and
forming a resist pattern by developing said resist film with a developer after irradiating, through a mask, said resist film with exposing light having a light component entering said resist film at the Brewster's angle,

wherein said chemically amplified resist material includes a dissolution inhibitor for generating carboxylic acid through irradiation with light and a base polymer for generating carboxylic acid through irradiation with light, and

wherein the dissolution inhibitor for generating carboxylic acid through irradiation with light is an ester of acrylic acid, methacrylic acid or α -trifluoromethylacrylic acid, and the base polymer for generating carboxylic acid through irradiation with light is an ester of polyacrylic acid, polymethacrylic acid or poly(α -trifluoromethylacrylic acid).

34-37. (Canceled)

38. (Previously presented) The pattern formation method of Claim 13,

wherein said exposing light is UV, KrF excimer laser, ArF excimer laser, F₂ laser, ArKr laser, Ar₂ laser, Kr₂ laser or extreme UV.

39. (Canceled)

40. (Previously presented) The pattern formation method of Claim 32,

wherein said exposing light is UV, KrF excimer laser, ArF excimer laser, F₂ laser, ArKr laser, Ar₂ laser, Kr₂ laser or extreme UV.

41. (Previously presented) The pattern formation method of Claim 33,

wherein said exposing light is UV, KrF excimer laser, ArF excimer laser, F₂ laser, ArKr laser, Ar₂ laser, Kr₂ laser or extreme UV.